Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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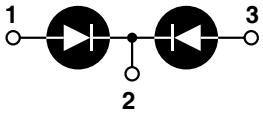
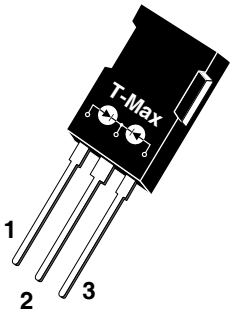


1 - Anode 1
2 - Common Cathode
Back of Case - Cathode
3 - Anode 2



Microsemi
POWER PRODUCTS GROUP

APT60S20B2CT(G) 200V 2X75A

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

HIGH VOLTAGE SCHOTTKY DIODE

PRODUCT APPLICATIONS	PRODUCT FEATURES	PRODUCT BENEFITS
• Parallel Diode -Switchmode Power Supply -Inverters	• Ultrafast Recovery Times	• Low Losses
• Free Wheeling Diode -Motor Controllers -Converters	• Soft Recovery Characteristics	• Low Noise Switching
• Snubber Diode	• Popular T-MAX™ Package	• Cooler Operation
• Uninterruptible Power Supply (UPS)	• Low Forward Voltage	• Higher Reliability Systems
• 48 Volt Output Rectifiers	• High Blocking Voltage	• Increased System Power Density
• High Speed Rectifiers	• Low Leakage Current	

MAXIMUM RATINGS

All Ratings Are Per Leg: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT60S20B2CT(G)	UNIT
V_R	Maximum D.C. Reverse Voltage	200	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_F(AV)$	Maximum Average Forward Current (T_C = 123°C, Duty Cycle = 0.5)	75	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	208	
I_{FSM}	Non-Repetitive Forward Surge Current (T_J = 45°C, 8.3ms)	600	
T_J,T_{STG}	Operating and StorageTemperature Range	-55 to 150	°C
T_L	Lead Temperature for 10 Sec.	300	
E_{VAL}	Avalanche Energy (2A, 30mH)	60	mJ

STATIC ELECTRICAL CHARACTERISTICS

Symbol			MIN	TYP	MAX	UNIT
V_F	Forward Voltage	I_F = 60A		.83	.90	Volts
		I_F = 120A		.98		
		I_F = 60A, T_J = 125°C		.72		
I_{RM}	Maximum Reverse Leakage Current	V_R = 200V			1	mA
		V_R = 200V, T_J = 125°C			25	
C_T	Junction Capacitance, V_R = 200V			300		pF

053-6043 Rev C 7-2006

DYNAMIC CHARACTERISTICS

APT60S20B2CT(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs V_R = 133V, T_C = 25°C	-	55		ns
Q_{rr}	Reverse Recovery Charge		-	160		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs V_R = 133V, T_C = 125°C	-	100		ns
Q_{rr}	Reverse Recovery Charge		-	490		nC
I_{RRM}	Maximum Reverse Recovery Current		-	10	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -700A/µs V_R = 133V, T_C = 125°C	-	80		ns
Q_{rr}	Reverse Recovery Charge		-	1100		nC
I_{RRM}	Maximum Reverse Recovery Current		-	27		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.30	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			40	
W_T	Package Weight		0.22		oz
			5.9		g

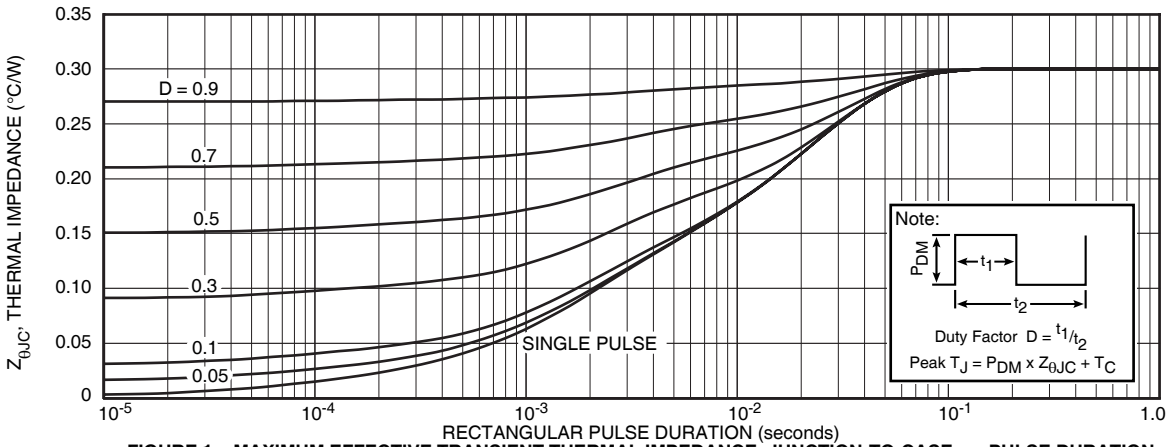


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

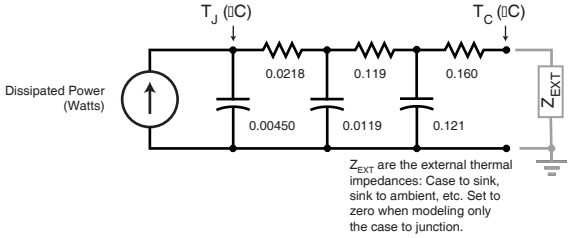


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

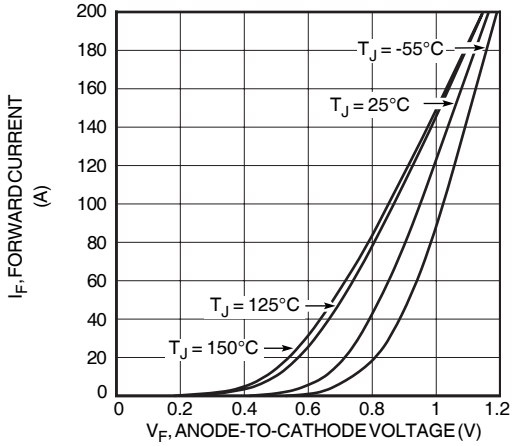


Figure 2. Forward Current *vs.* Forward Voltage

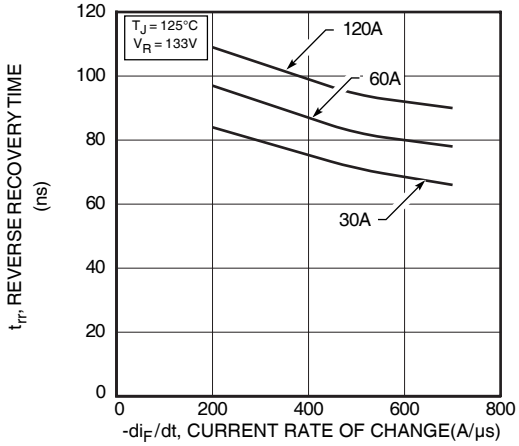


Figure 3. Reverse Recovery Time *vs.* Current Rate of Change

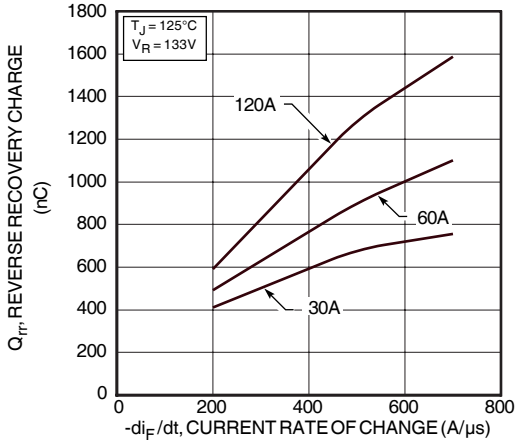


Figure 4. Reverse Recovery Charge *vs.* Current Rate of Change

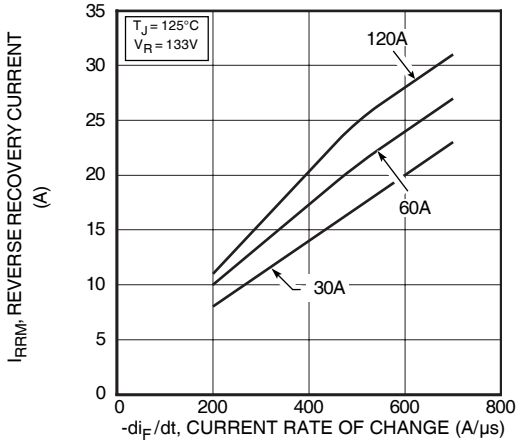


Figure 5. Reverse Recovery Current *vs.* Current Rate of Change

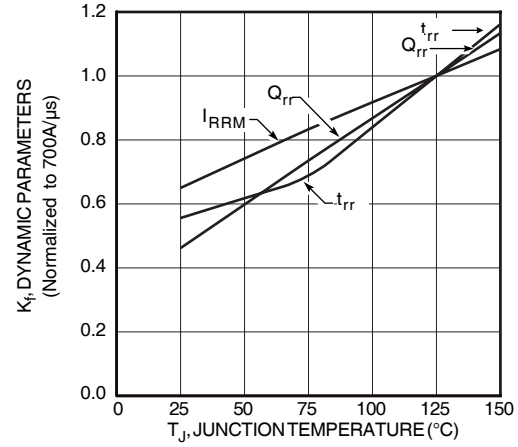


Figure 6. Dynamic Parameters *vs.* Junction Temperature

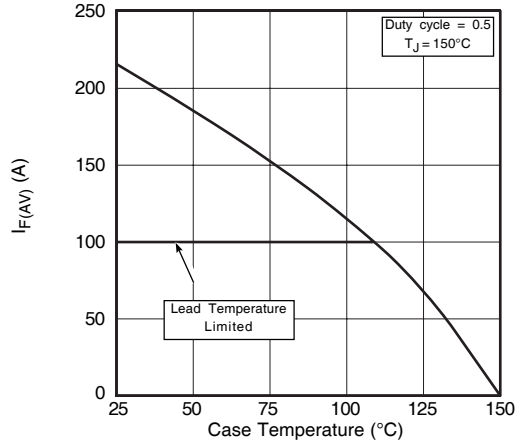


Figure 7. Maximum Average Forward Current *vs.* CaseTemperature

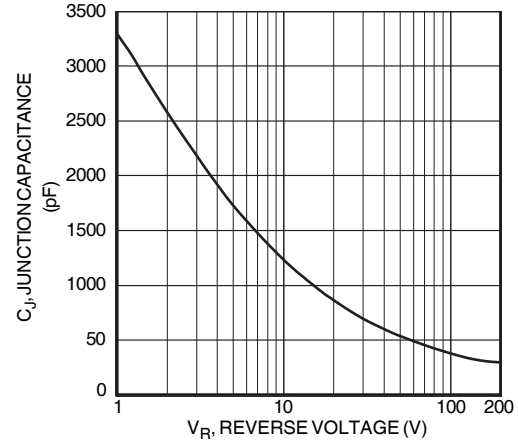


Figure 8. Junction Capacitance *vs.* Reverse Voltage

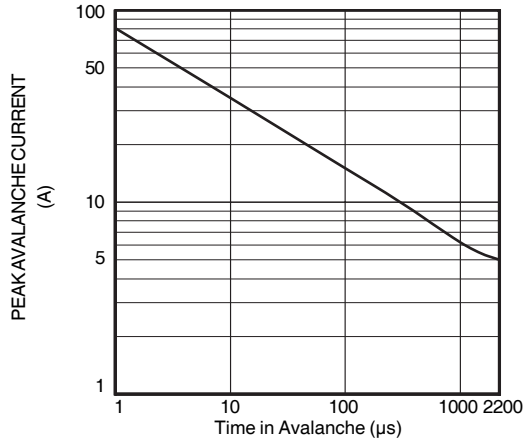


Figure 9. Single Pulse UIS SOA

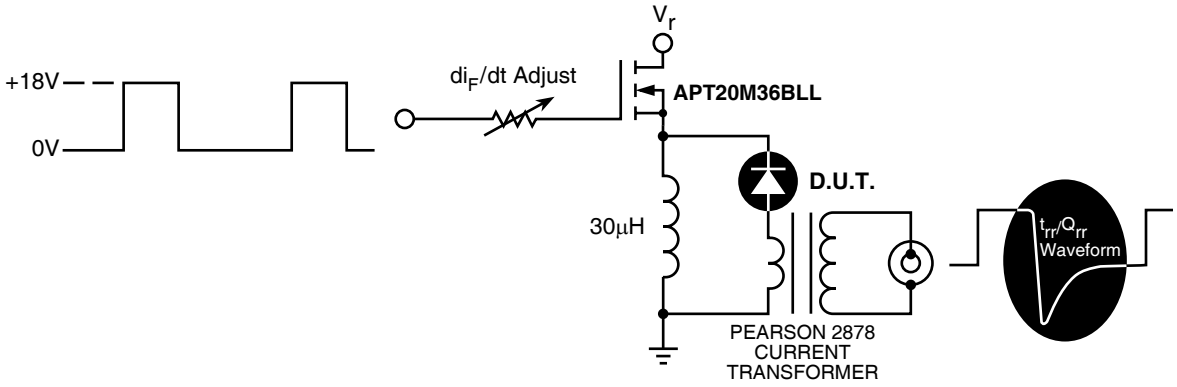
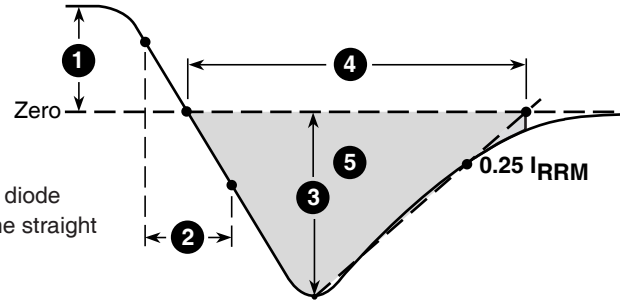


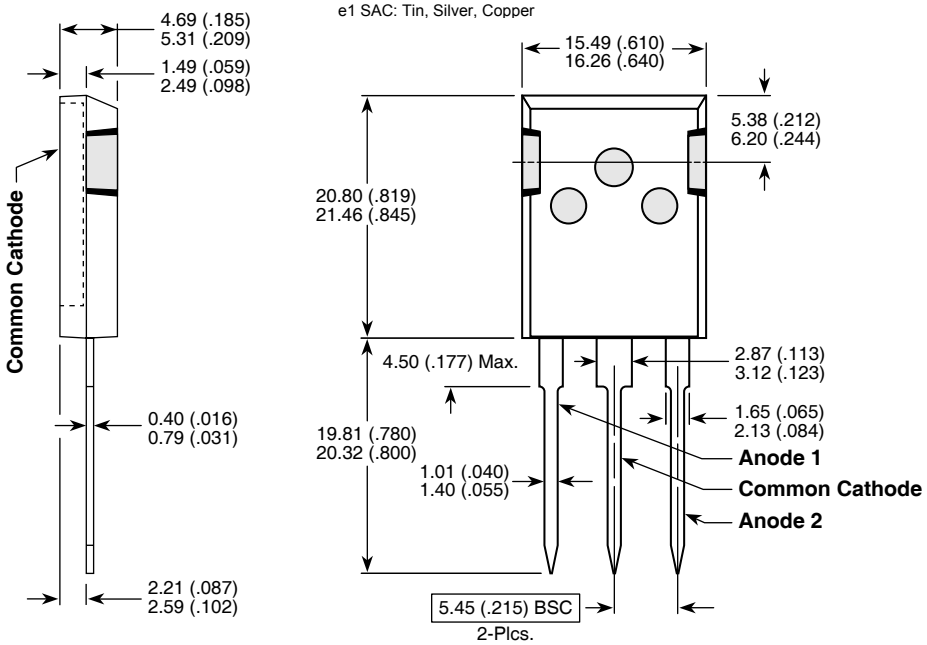
Figure 9. Diode Test Circuit



1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

Figure 10, Diode Reverse Recovery Waveform and Definitions

T-MAX™ (B2) Package Outline



Dimensions in Millimeters and (Inches)